

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

MRF340 is Designed for VHF Radios that use Collector Modulation in the Driver/Final Amplifiers to Produce an Amplitude Modulated Signal.

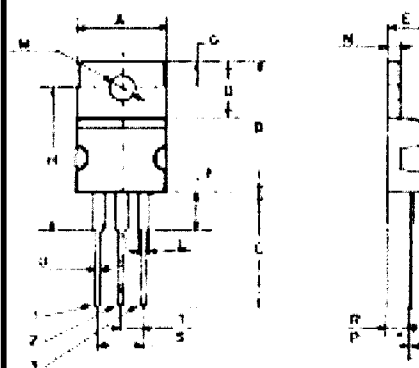
FEATURES INCLUDE:

- Replaces Original **MRF340** in Most Applications
- High Gain Reduces Drive Requirements
- Economical **TO-220CE** Package

MAXIMUM RATINGS

I_C	1.0 A
V_{CES}	50 V
P_{DISS}	12.5 W @ $T_C = 25^\circ C$
T_{STG}	$-55^\circ C$ to $+150^\circ C$
θ_{JC}	10 $^\circ C/W$

PACKAGE STYLE TO-220AB (COMMON EMITTER)



1 = BASE
2 = EMITTER
3 = COLLECTOR TAB = EMITTER

	DIMENSIONS			
	mm		inches	
	min	max	min	max
A	10	10.4	0.393	0.409
B	15.2	15.9	0.598	0.626
C	12.7	13.7	0.500	0.539
D	6.2	6.6	0.244	0.260
E	4.4	4.8	0.173	0.181
F	3.5	5.5	0.137	0.216
G	2.65	2.95	0.104	0.116
H	17.6 typ.		0.692 typ.	
L	1.14	1.7	0.044	0.067
M	3.75	3.85	0.147	0.151
N	1.23	1.32	0.048	0.051
P	0.41	0.64	0.016	0.025
R	2.4	2.72	0.094	0.107
S	4.95	5.15	0.194	0.203
T	2.4	2.7	0.094	0.106
U	0.61	0.94	0.024	0.037

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 50$ mA		50			V
BV_{CBO}	$I_C = 10$ mA		50			V
BV_{EBO}	$I_E = 5.0$ mA		4.0			V
I_{CES}	$V_{CES} = 25$ V				1.0	mA
h_{FE}	$V_{CE} = 10$ V	$I_C = 100$ mA	10		200	---
C_{OB}	$V_{CB} = 30$ V	$f = 1.0$ MHz		15		pF
G_{PE}	$V_{CC} = 13.5$ V	$P_{out} = 2.0$ W		10		dB
G_{PE}	$V_{CC} = 27$ V	$P_{out} = 8.0$ W _{pk}	13.0	15.0		dB
η				55		%

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